

Title (en)
HIGH SPEED SILICON ETCHING METHOD

Title (de)
SCHNELLES SILIZIUMÄTZVERFAHREN

Title (fr)
PROCEDE DE GRAVURE DE SILICIUM A VITESSE ELEVEE

Publication
EP 1329948 A1 20030723 (EN)

Application
EP 01967676 A 20010913

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Abstract (en)
This invention provides the following high-rate silicon etching method. An object to be processed W having a silicon region is so set as to be in contact with a process space in a process chamber that can be held in vacuum. An etching gas is introduced into the process space to form a gas atmosphere at a gas pressure of 13 Pa to 1,333 Pa (100 mTorr to 10 Torr). A plasma is generated upon application of RF power. In the plasma, the sum of the number of charged particles such as ions and the number of radicals increases, and etching of the silicon region is performed at a higher rate than in conventional etching. <IMAGE>

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H01L 21/3065

IPC 8 full level
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Cited by
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